

# 2SC4892

## Silicon NPN triple diffusion planar type

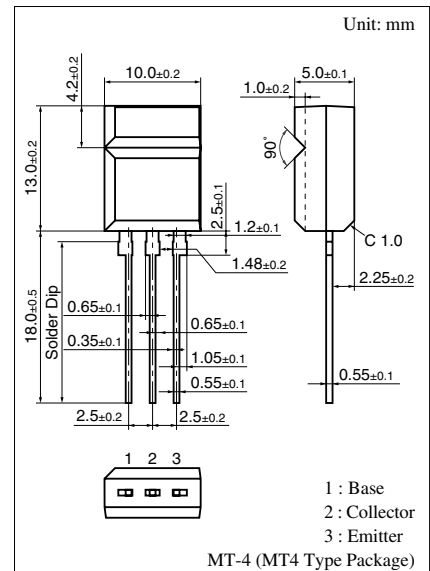
For power switching

### ■ Features

- High-speed switching
- High collector to base voltage  $V_{CBO}$
- Satisfactory linearity of forward current transfer ratio  $h_{FE}$
- Allowing supply with the radial taping

### ■ Absolute Maximum Ratings $T_C = 25^\circ\text{C}$

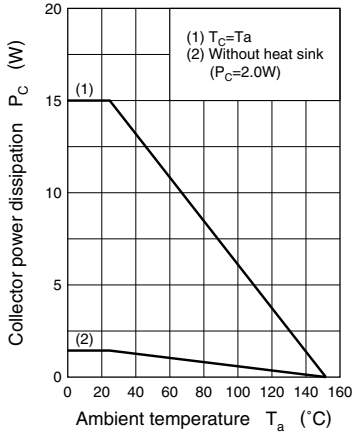
Parameter	Symbol	Rating	Unit	
Collector to base voltage	$V_{CBO}$	900	V	
Collector to emitter voltage	$V_{CES}$	900	V	
	$V_{CEO}$	800	V	
Emitter to base voltage	$V_{EBO}$	7	V	
Peak collector current	$I_{CP}$	2	A	
Collector current	$I_C$	1	A	
Base current	$I_B$	0.3	A	
Collector power dissipation	$T_C = 25^\circ\text{C}$	$P_C$	15	W
	$T_a = 25^\circ\text{C}$		2	
Junction temperature	$T_j$	150	$^\circ\text{C}$	
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$	



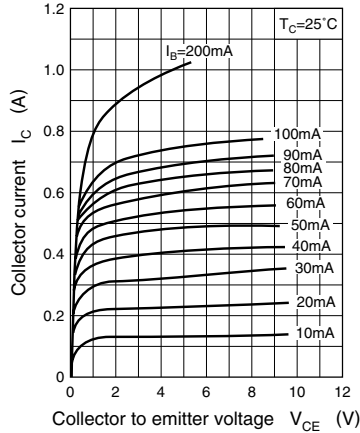
### ■ Electrical Characteristics $T_C = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector cutoff current	$I_{CBO}$	$V_{CB} = 900\text{ V}, I_E = 0$			50	$\mu\text{A}$
Emitter cutoff current	$I_{EBO}$	$V_{EB} = 7\text{ V}, I_C = 0$			50	$\mu\text{A}$
Collector to emitter voltage	$V_{CEO}$	$I_C = 1\text{ mA}, I_B = 0$	800			V
Forward current transfer ratio	$h_{FE1}$	$V_{CE} = 5\text{ V}, I_C = 0.05\text{ A}$	6			
	$h_{FE2}$	$V_{CE} = 5\text{ V}, I_C = 0.5\text{ A}$	3			
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = 0.2\text{ A}, I_B = 0.04\text{ A}$			1.5	V
Base to emitter saturation voltage	$V_{BE(sat)}$	$I_C = 0.2\text{ A}, I_B = 0.04\text{ A}$			1	V
Transition frequency	$f_T$	$V_{CE} = 10\text{ V}, I_C = 0.05\text{ A}, f = 1\text{ MHz}$		4		MHz
Turn-on time	$t_{on}$	$I_C = 0.2\text{ A}, I_{B1} = 0.04\text{ A}, I_{B2} = -0.08\text{ A}, V_{CC} = 250\text{ V}$			1	$\mu\text{s}$
Storage time	$t_{stg}$				3	$\mu\text{s}$
Fall time	$t_f$				1	$\mu\text{s}$

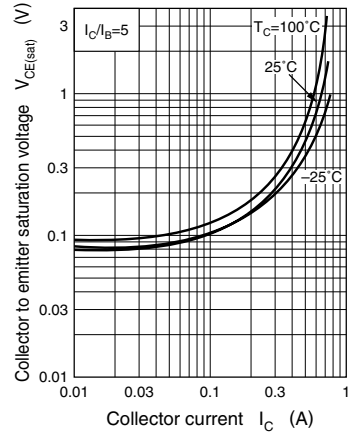
$P_C - T_a$



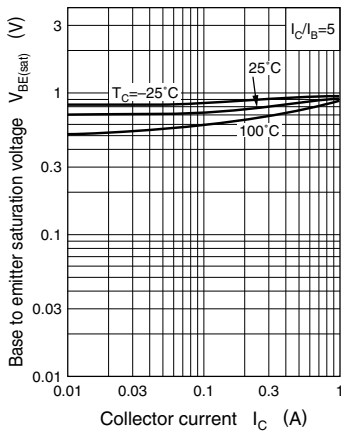
$I_C - V_{CE}$



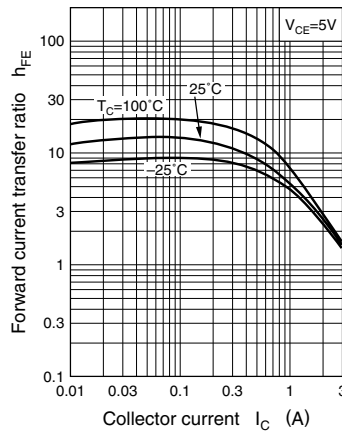
$V_{CE(sat)} - I_C$



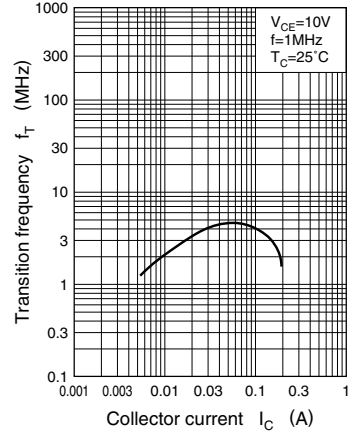
$V_{BE(sat)} - I_C$



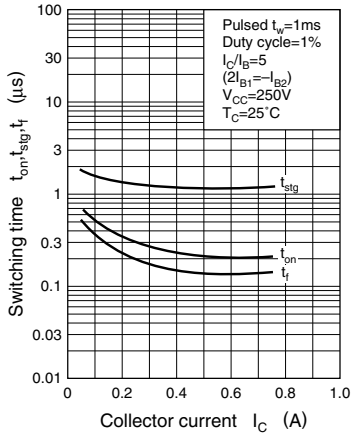
$h_{FE} - I_C$



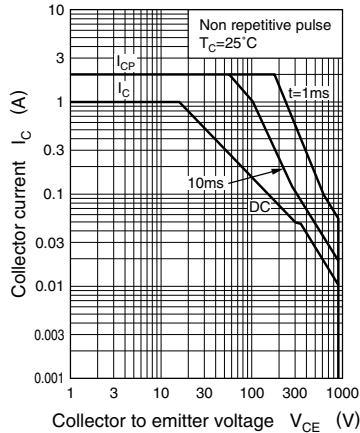
$f_T - I_C$



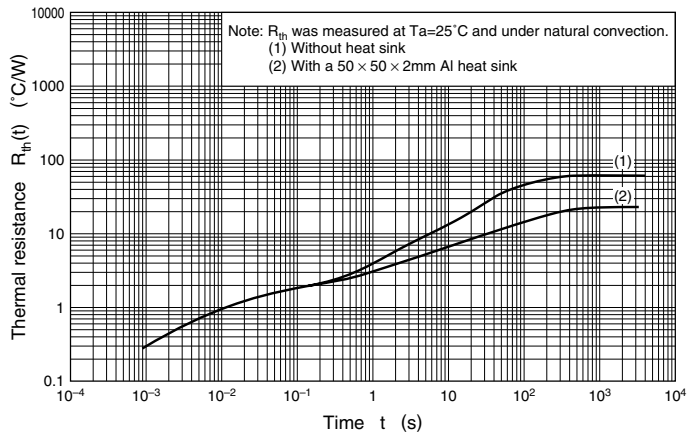
$t_{on}, t_{stg}, t_f - I_C$



Area of safe operation (ASO)



$$R_{th(t)} - t$$



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